

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	672	(first adj3 wiring adj3 layer) and (second adj3 wiring adj3 layer) and (third adj3 wiring adj3 layer)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 11:24
2	BRS	L2	243	1 and (gate adj3 electrode)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 12:11
3	BRS	L3	136	(first adj3 wiring adj3 layer) adj10 (gate adj3 electrode)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 12:15
4	BRS	L4	45	2 and 3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 12:15

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	672	(first adj3 wiring adj3 layer) and (second adj3 wiring adj3 layer) and (third adj3 wiring adj3 layer)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 11:24
2	BRS	L2	243	1 and (gate adj3 electrode)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 12:11
3	BRS	L3	136	(first adj3 wiring adj3 layer) adj10 (gate adj3 electrode)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 12:15
4	BRS	L4	45	2 and 3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 13:51
5	BRS	L19	512	third adj wiring adj layer	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 13:52

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L20	323	19 same (first adj wiring adj layer)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 14:47
7	BFS	L22	1288	(pattern or patterned or patterning) same (first adj3 wiring adj3 layer)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 15:37
8	BRS	L23	696	22 same (second adj3 wiring adj3 layer)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 15:38
9	BRS	L24	44	23 and 3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 15:56
10	IS&R	L25	179	(438/200).CCLS.	USPAT	2002/12/05 15:59
11	IS&R	L32	508	(438/710).CCLS.	USPAT	2002/12/05 16:49
12	BRS	L33	658	(third adj wiring) same (first adj wiring) same (second adj wiring)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 16:57

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L34	30	(first adj wiring) adj3 (connect or connecting or connected) adj3 (gate adj electrode)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 16:59
14	BRS	L35	10	33 and 34	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/12/05 17:00
15	IS&R	L36	88	(438/737).CCLS.	USPAT	2002/12/05 17:20

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	IS&R	L1	551	(438/197).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/06/10 15:21

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TITLE: Multilayered inverter structure of complementary metal oxide semiconductor device - has first wiring layer linked to refractory metal silicide gate electrode and second and third wiring layer extending via insulation layer on source and drain of P-MOS and N-MOS, respectively

----- KWIC -----

NOVELTY - A first wiring layer is linked to a gate electrode refractory metal silicide layer and a second wiring layer extends via an insulation film on each source and drain diffusion layer of PMOS transistor. A third wiring layer extends via insulating film on N channel source and drain of NMOS transistor.

DETAILED DESCRIPTION - Refractory metal silicide layers are formed on the drains of P channel and N channel MOS transistors. The refractory metal silicide layer consists of the gate electrode for P channel and N channel MOS transistors.

ADVANTAGE - The drain wiring can be formed on same layer as gate electrode, so aspect ratio of contact to source area of source wiring becomes less. Miniaturization of circuit is attained.

Multilayered inverter structure of complementary metal oxide semiconductor device - has first wiring layer linked to refractory metal

silicide gate

electrode and second and third wiring layer extending via
insulation layer on
source and drain of P-MOS and N-MOS, respectively

MULTILAYER INVERTER STRUCTURE COMPLEMENTARY METAL OXIDE
SEMICONDUCTOR DEVICE

FIRST WIRE LAYER LINK REFRACTORY METAL SILICIDE GATE

ELECTRODE SECOND THIRD

WIRE LAYER EXTEND INSULATE LAYER SOURCE DRAIN P MOS N MOS
RESPECTIVE